

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	12485	((438/26) or (438/51) or (438/98) or (438/100) or (438/101) or (438/106) or (438/107) or (438/597) or (438/653) or (438/669) or (438/670) or (438/685) or (438/686) or (438/687) or (438/692)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/15 20:10
L2	2	1 and ((trench near5 (substrate\$1 or wafer\$1)) same catalyst)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/15 20:10
L3	12485	((438/26) or (438/51) or (438/98) or (438/100) or (438/101) or (438/106) or (438/107) or (438/597) or (438/653) or (438/669) or (438/670) or (438/685) or (438/686) or (438/687) or (438/692)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/15 20:11
L4	1127	L3 and (trench near5 (substrate\$1 or wafer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/15 20:11
L5	521	4 and (bond\$3 or abut\$3 or combin\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/15 20:11
L6	3	5 and (trench same catalyst)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/15 20:12
S1	11679	((438/26) or (438/51) or (438/98) or (438/100) or (438/101) or (438/106) or (438/107) or (438/597) or (438/653) or (438/669) or (438/670) or (438/685) or (438/686) or (438/687) or (438/692)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/15 20:10

S2	2	S1 and ((trench near5 (substrate\$1 or wafer\$1)) same catalyst)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/15 20:11
S3	12	S1 and (trench same catalyst)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/15 20:11
S4	10	S3 not S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/13 00:52
S5	34	((trench near5 (substrate\$1 or wafer\$1)) same catalyst)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/13 00:56
S6	34	S5 not S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/13 00:57
S7	7	trench\$1 near2 (((first and second) or (top and bottom) or two) near2 (substrate\$1 or wafer\$1) and (abutment or border))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 11:25
S8	3	trench\$1 near2 (((first and second) or (top and bottom) or two) near2 (substrate\$1 or wafer\$1) and abutment )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 11:15
S9	11	("4426129"   "4578097"   "4709986"   "4896930"   "4904052"   "5263111"   "5333229"   "5366530"   "5465860"   "5770465"   "6097870").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/11/14 11:16
S10	1	("6624077").URPN.	USPAT	OR	OFF	2004/11/14 11:17

S11	559	trench\$1 near2 (((first and second) or (top and bottom) or two) near2 (substrate\$1 or wafer\$1) )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 11:26
S12	211	S11 and (bond\$3 or abut\$3 or combin\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/15 20:11
S13	2	S12 and catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 12:25
S14	3	(("5935430") or ("6406636") or ("6537087")).PN.	USPAT	OR	OFF	2004/11/14 11:42
S15	27	("3530568"   "3538744"   "3678570"   "3732982"   "4220276"   "4245769"   "4474889"   "4551251"   "4865729"   "4891120"   "4905497"   "4908112"   "4935040"   "5114551"   "5116495"   "5132012"   "5194133"   "5236118"   "5453769"   "5500071"   "5567868"   "5571410"   "5595650"   "5792943"   "5888390").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/11/14 11:42
S16	7	("5935430").URPN.	USPAT	OR	OFF	2004/11/14 11:44
S17	4	("20020126459"   "5935430"   "6406636"   "6537087").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/11/14 11:44
S18	0	("6667225").URPN.	USPAT	OR	OFF	2004/11/14 11:45
S19	5	catalyst same (platinum or lead) same trench\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 11:58
S20	120	catalyst same trench\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 11:58

S21	45	S20 and (platinum or lead)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 12:03
S22	5	S20 same (platinum or lead)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 12:03
S23	27135	catalyst same (remov\$3 near5 gas\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 12:27
S24	0	S23 same trench\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 12:26
S25	77	S23 and trench\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 12:26
S26	5	catalyst near5 (lin\$3 same trench\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 12:29
S27	52	catalyst same (lin\$3 same trench\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 12:30
S28	9	S27 and (platinum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 12:30
S29	1	("6667225").PN.	USPAT	OR	OFF	2004/11/15 19:24

S30	0	(catalyst\$1 near3 (layer or film or material or lin\$3)) same trench\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 19:39
S31	70	(catalyst near3 (layer or film or material or lin\$3)) same trench\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 19:38
S32	6	S31 and (remov\$3 near4 gas\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 19:35
S33	0	S31 same (remov\$3 near4 gas\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 19:36
S34	0	S31 same (remov\$3 with gas\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 19:36
S35	4	S31 same (remov\$3 same gas\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 19:40
S36	0	S31 and (micro near2 channel\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 19:39
S37	44	(micro near2 channel\$1) same (remov\$3 same gas\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 19:39

S38	0	S37 same (catayst\$1 near3 (layer or film or material or lin\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 19:40
S39	0	S37 and (catayst\$1 near3 (layer or film or material or lin\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 19:41
S40	0	S37 and (catayst\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 19:44
S41	8	(channel\$1 near2 trench\$2) and (catalyst near3 (layer or film or material or lin\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 19:47
S42	2217	(trench\$1 or channel\$1) same (catalyst near3 (layer or film or material or lin\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 21:01
S43	481	(trench\$1 or channel\$1) near5 (catalyst near3 (layer or film or material or lin\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 21:04
S44	1	S43 and (recombiner)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 21:05
S45	26	S43 and ((silicon near2 substrate\$1) or wafer\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 21:25
S46	1	("20030164231").PN.	US-PGPUB; USPAT	OR	OFF	2004/11/17 20:22
S47	1	("20030062149").PN.	US-PGPUB; USPAT	OR	OFF	2004/11/17 20:20

S48	0	("2003/0164231").URPN.	USPAT	OR	OFF	2004/11/17 20:23
S49	10111	copper near2 bond\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 20:53
S50	4	(copper near2 bond\$3) same ((silicon near2 substrate\$1) or wafer\$1) same trench\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 20:56
S51	0	((copper near2 bond\$3) near4 ((silicon near2 substrate\$1) or wafer\$1)) same trench\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 20:56
S52	0	((copper near2 bond\$3) near10 ((silicon near2 substrate\$1) or wafer\$1)) same trench\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 20:56
S53	4	((copper near2 bond\$3) same ((silicon near2 substrate\$1) or wafer\$1)) same trench\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 20:56
S54	17	((copper near2 bond\$3) and ((silicon near2 substrate\$1) or wafer\$1)) same trench\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 20:59
S55	13	S54 not S53	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 20:57
S56	0	((copper near2 bond\$3) with ((silicon near2 substrate\$1) or wafer\$1)) same trench\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 20:59

S57	668	(copper near5 ((silicon near2 substrate\$1) or wafer\$1)) same (bond\$3 or combin\$3 or join\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 21:01
S58	208	S57 and (trench\$2 or groov\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 16:05
S59	11	S58 and (catalyst)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 21:05
S60	197	S58 not S59	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/17 21:05
S61	8	("4689113"   "5241450"   "5366906"   "5419806"   "5880010"   "6255726"   "6355501"   "6355976").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/11/17 21:13
S62	0	("6661085").URPN.	USPAT	OR	OFF	2004/11/17 21:14
S63	13762	(pb or lead) near5 catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:13
S64	1	S63 same trench\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 14:47
S65	47	S63 and trench\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 14:47



S66	6603	(pb or lead) near2 catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:08
S67	3125	(pb or lead) near catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:08
S68	59	S67 and (trench\$2 or groove\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:09
S69	267	S67 and (trench\$2 or groove\$1 or channel\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:09
S70	208	S69 not S68	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 16:14
S71	1097	pb near5 catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 21:08
S72	6	pb near2 (catalyst near2 (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:21
S73	943	(deposit\$3 or lin\$3 near2 (pb or lead)) near2 (catalyst near2 (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:25

S74	3443	((deposit\$3 or lin\$3) near2 (pb or lead)) same (trench\$2 or groove\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:30
S75	11	S74 same catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:28
S76	37	((deposit\$3 or lin\$3) near2 (pb)) same (trench\$2 or groove\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:32
S77	3	S76 and catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:31
S78	32	((deposit\$3 or lin\$3) near (pb or lead)) near (trench\$2 or groove\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:53
S79	0	((deposit\$3 or lin\$3) near ((pb or lead) near2 material)) near (trench\$2 or groove\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:35
S80	13	((deposit\$3 or lin\$3) near ((pb or lead) near2 material)) same (trench\$2 or groove\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:38
S81	1	S80 and catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:36

S82	6	(deposit\$3 near ((pb or lead near2 material)) same (trench\$2 or groove\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:42
S83	0	((deposit\$3 near ((pb or lead near2 material)) near5 catalyst) same (trench\$2 or groove\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:42
S84	0	((deposit\$3 near ((pb or lead near2 material)) near5 catalyst) and (trench\$2 or groove\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:43
S85	0	((deposit\$3 near ((pb or lead near2 material)) same catalyst) and (trench\$2 or groove\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:43
S86	3	((deposit\$3 near ((pb or lead near2 material)) same catalyst)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:44
S87	3	((deposit\$3 near ((pb or lead near2 material)) near10 catalyst)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 15:44
S88	673	(copper near5 ((silicon near2 substrate\$1) or wafer\$1)) same (bond\$3 or combin\$3 or join\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 19:16
S89	212	S88 and (trench\$2 or groov\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 16:05

S90	3	S89 and ((lift near2 off) same resist)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 16:08
S91	16	S89 and (lift near2 off)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 16:08
S92	13	S91 not S90	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 16:08
S93	2	S67 and (lift near2 off)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 16:15
S94	0	(lift near2 off) same (remove near2 copper) same catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 16:17
S95	3	(lift near2 off) same (copper) same catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 16:19
S96	708	(lift near2 off) same copper	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 16:19
S97	46	S96 and catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 16:19

S98	48	(mask\$3 near5 catalyst) same copper	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:16
S99	0	S98 and (lift near2 off)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:13
S100	549	((mask\$3 or protect\$3 or insulat\$3) near5 catalyst) same copper	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:18
S101	4	S100 and (lift near2 off)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:17
S102	793	((mask\$3 or protect\$3 or insulat\$3 or cover\$3) near5 catalyst) same copper	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:19
S103	4	S102 and (lift near2 off)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:18
S104	381	((mask\$3 or protect\$3 or insulat\$3 or cover\$3) near2 catalyst) same copper	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:23
S105	1	S104 and (lift near2 off)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:20

S10 6	3	S104 and (trench\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:21
S10 7	52	((mask\$3 or protect\$3 or insulat\$3 or cover\$3) near2 catalyst) near3 copper	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:27
S10 8	185	((mask\$3 or protect\$3 or insulat\$3 or cover\$3) near2 catalyst) same channel\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:34
S10 9	2739	((mask\$3 or protect\$3 or insulat\$3 or cover\$3) near2 catalyst) same (form\$3 or etch\$3 or creat\$3 near2 channel\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:35
S11 0	20	((mask\$3 or protect\$3 or insulat\$3 or cover\$3) near2 catalyst) same ((form\$3 or etch\$3 or creat\$3) near2 channel\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:38
S11 1	5	((mask\$3 or protect\$3) near2 catalyst) same ((form\$3 or etch\$3 or creat\$3) near2 channel\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 18:39
S11 2	1	("5424252").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/11/19 18:45
S11 3	0	("6607981").URPN.	USPAT	OR	OFF	2004/11/19 18:45
S11 4	57	(copper near2 wafer) near2 bond\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 21:51

S11 5	296	(copper adj copper) near2 bond\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 19:17
S11 6	59	S115 same (wafer\$2 or substrate\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 19:17
S11 7	1	("6607981").PN.	USPAT	OR	OFF	2004/11/19 20:58
S11 8	6	pb near2 (catalyst near2 (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 21:11
S11 9	1	("5424252").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/11/19 21:10
S12 0	419	pb near2 catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 21:11
S12 1	101	pb adj catalyst	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 21:16
S12 2	0	((pb or lead) adj (layer or film)) near3 (catalyst near2 (layer or film))) same (trench\$2 or groov\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 21:19
S12 3	0	((pb or lead) adj (layer or film)) same (catalyst near2 (layer or film))) same (trench\$2 or groov\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 21:19

S12 4	0	((pb or lead) adj (layer or film)) with (catalyst near2 (layer or film))) same (trench\$2 or groov\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 21:19
S12 5	0	((pb or lead) adj (layer or film)) and (catalyst near2 (layer or film))) same (trench\$2 or groov\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 21:20
S12 6	8	((pb or lead) same (catalyst near2 (layer or film))) same (trench\$2 or groov\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 21:20
S12 7	1568	(copper near2 (bond\$3 or combin\$3)) near5 (wafer\$1 or substrate\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 22:18
S12 8	206	S127 and (trench\$2 or groov\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 21:53
S12 9	0	(copper adj to adj copper) near2 bond\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/19 22:18